
HSU276

Silicon Schottky Barrier Diode for Mixer

HITACHI

ADE-208-078F(Z)
Rev 6

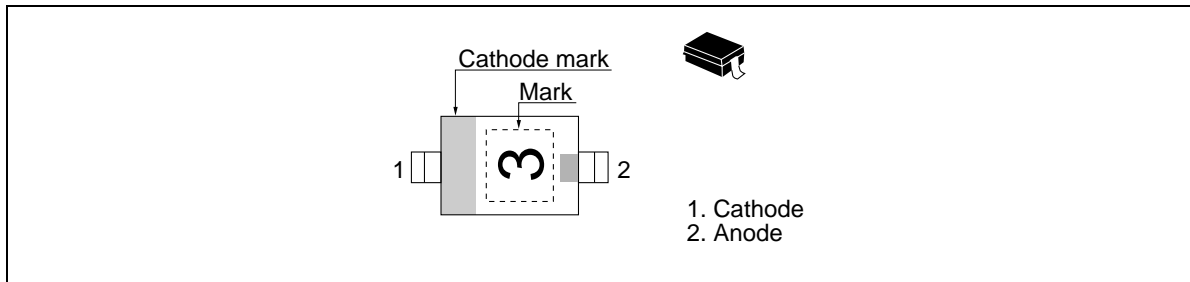
Features

- High forward current, Low capacitance.
- Ultra small Resin Package (URP) is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HSU276	3	URP

Outline



HSU276

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Reverse voltage	V_R	3	V
Average rectified current	I_o	30	mA
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-55 to +125	°C

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse voltage	V_R	3	—	—	V	$I_R = 1 \text{ mA}$
Reverse current	I_R	—	—	50	μA	$V_R = 0.5\text{V}$
Forward current	I_F	35	—	—	mA	$V_F = 0.5\text{V}$
Capacitance	C	—	—	0.85	pF	$V_R = 0.5\text{V}, f = 1 \text{ MHz}$
ESD-Capability ¹	—	30	—	—	V	C = 200pF , Both forward and reverse direction 1 pulse.

Note: 1. Failure criterion ; $I_R \geq 100\mu\text{A}$ at $V_R = 0.5 \text{ V}$

Main Characteristic

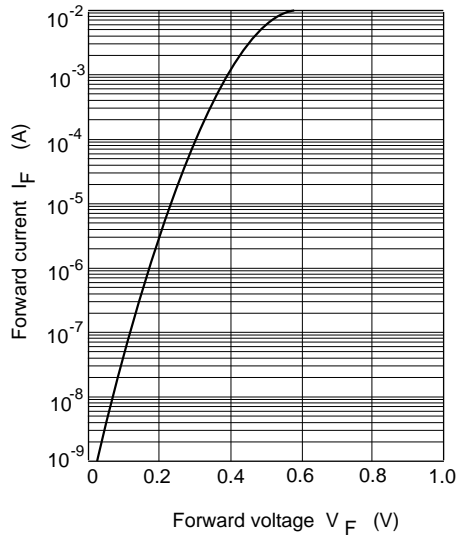


Fig.1 Forward current Vs. Forward voltage

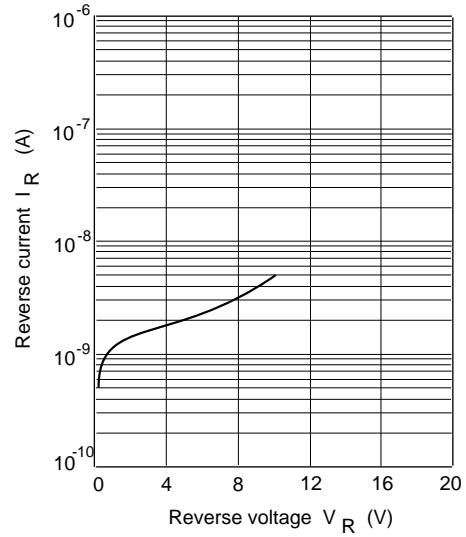


Fig.2 Reverse current Vs. Reverse voltage

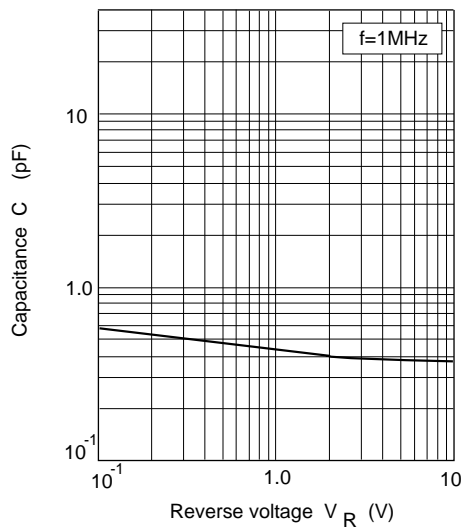


Fig.3 Capacitance Vs. Reverse voltage

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Package Dimensions

Unit : mm

